

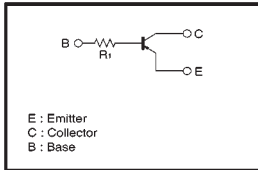
Digital transistors (built-in resistor)

DTA115TE / DTA115TUA / DTA115TKA / DTA115TSA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

●Circuit schematic



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	—50	—	—	V	$I_C = -50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	—50	—	—	V	$I_C = -1 mA$
Emitter-base breakdown voltage	BV_{EBO}	—5	—	—	V	$I_E = -50 \mu A$
Collector cutoff current	I_{CBO}	—	—	—0.5	μA	$V_{CB} = -50V$
Emitter cutoff current	I_{EBO}	—	—	—0.5	μA	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	—0.3	V	$I_C/I_E = -1 mA/-0.1 mA$
DC current transfer ratio	h_{FE}	100	250	600	—	$I_C = -1 mA, V_{CE} = -5V$
Input resistance	R_i	70	100	130	k Ω	—
Transition frequency	f_T	—	250	—	MHz	$V_{CE} = -10V, I_E = 5mA, f = 100MHz$ *

* Transition frequency of the device.

(96-259-A115T)

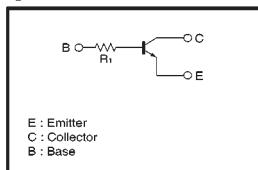
Digital transistors (built-in resistor)

DTC115TUA / DTC115TKA / DTC115TSA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

●Circuit schematic



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	50	—	—	V	$I_C = 50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	—	V	$I_C = 1 mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E = 50 \mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 50V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C/I_E = 1 mA/0.1 mA$
DC current transfer ratio	h_{FE}	100	250	600	—	$I_C = 1 mA, V_{CE} = 5V$
Input resistance	R_i	70	100	130	k Ω	—
Transition frequency	f_T	—	250	—	MHz	$V_{CE} = 10V, I_E = -5mA, f = 100MHz$ *

* Transition frequency of the device.

(96-317-C115T)

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	—50	V
Collector-emitter voltage	V_{CEO}	—50	V
Emitter-base voltage	V_{EBO}	—5	V
Collector current	I_C	—100	mA
Collector power dissipation	Pc	150	mW
		200	
		300	
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	—55~+150	°C

●Package, marking, and packaging specifications

Part No.	DTA115TE	DTA115TUA	DTA115TKA	DTA115TSA
Package	EMT3	UMT3	SMT3	SPT
Marking	99	99	99	—
Packaging code	TL	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	3000	5000

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	Pc	200	mW
		300	
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	—55~+150	°C

●Package, marking, and packaging specifications

Part No.	DTC115TUA	DTC115TKA	DTC115TSA
Package	UMT3	SMT3	SPT
Marking	09	09	—
Packaging code	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	5000